



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the application of:

KONNO et al.

Serial Number: 07/743,383

Group Art Unit: 1104

Filed: August 21, 1991

Examiner: G. Goudreau

For: METHOD FOR PRODUCING SEMICONDUCTOR INTEGRATED CIRCUITS AND APPARATUS USED IN SUCH METHOD

RESPONSE UNDER 37 CFR 1.115

Honorable Commissioner
of Patents and Trademarks
Washington, D.C. 20231

June 29, 1994

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JUL 05 1994

Dear Sir:

GROUP 1100

In response to the Office Action dated April 5, 1994,
kindly amend the above identified patent application as follows:

IN THE CLAIMS:

1. (Thrice Amended) A method for producing semiconductor integrated circuits, comprising the steps of:

a first step of selectively etching a metallic film formed on a surface of a substrate and exposed through a mask made of a resist which selectively covers said metallic film, by effectively contacting said [metal] metallic film exposed through said mask with a gaseous etchant comprising chlorine, bromine, or a compound thereof; and

a second step of removing the mask used in said etching by effectively ashing said mask, by contacting said mask with a plasma generated in an atmosphere comprising oxygen gas and water vapor under conditions sufficient to also remove etchant components remaining strongly attached to and in effective contact with said metallic film or said substrate down to a residual

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attach
m.H.
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M.M.
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